

Amendments to the Specification:

Please replace the paragraph beginning at page 20, line 10, with the following amended paragraph:

Figs. 4A-4C 4A-4D are cross-sectional views of the epitaxial junction isolation (epi-JI) of CMOS, bipolar and DMOS components using deep "down-only" isolation diffusions;

Please replace the paragraph beginning at page 64, line 25, (as previously amended) with the following amended paragraph:

Referring to **Fig. 18B-3**, an NPN 312 has a base which includes a P base region 395B (which is formed with a specific mask), an isolated region 392B of substrate 350, and a P+ base contact region 364L. The emitter of NPN 312 is an N region 378L. The collector is an N isolation region 354K, which merges with a deep N layer 390D. Unlike NPN 305 in **Fig. 18A-3**, which has a section of field oxide layer 352 between the base and the emitter, ~~emitter~~ and P N well 372C underlying the field oxide layer 352, in NPN 312 the entire area is active and ~~no N well is necessary~~. As a result, the base-to-emitter capacitance of NPN 312 is greater than the base-to-emitter capacitance of NPN 305.